Computational Microelectronics

Assignment #6

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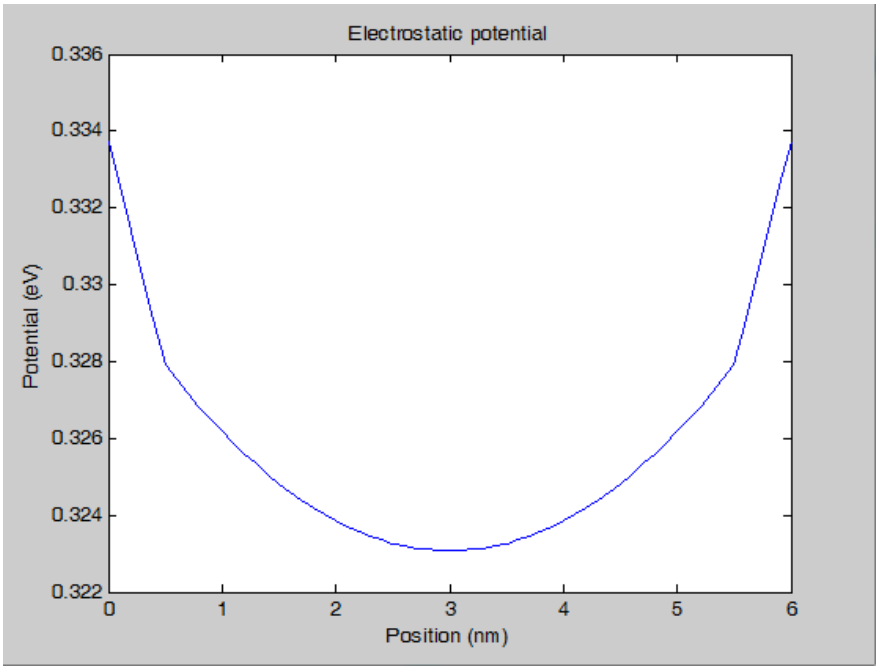
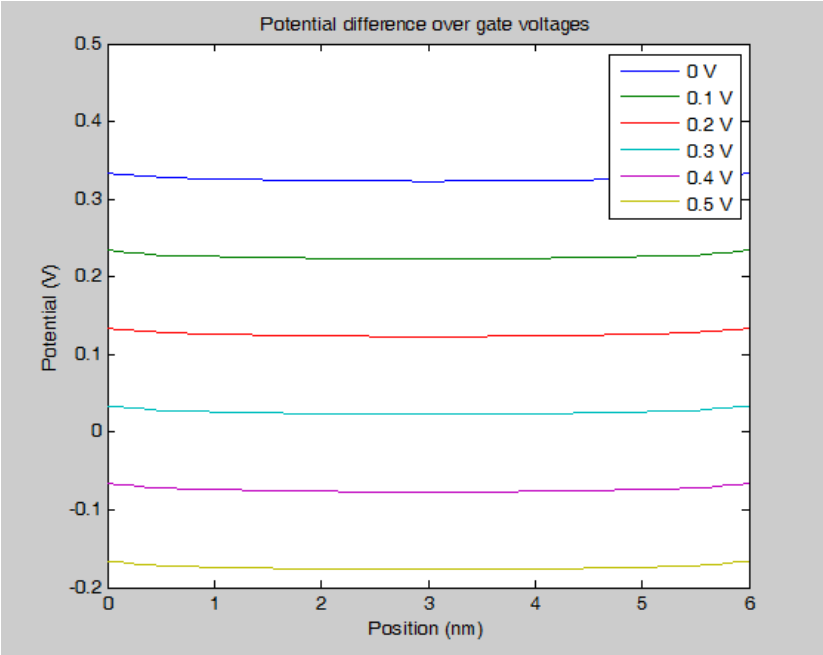
1. Electrostatic potential at position

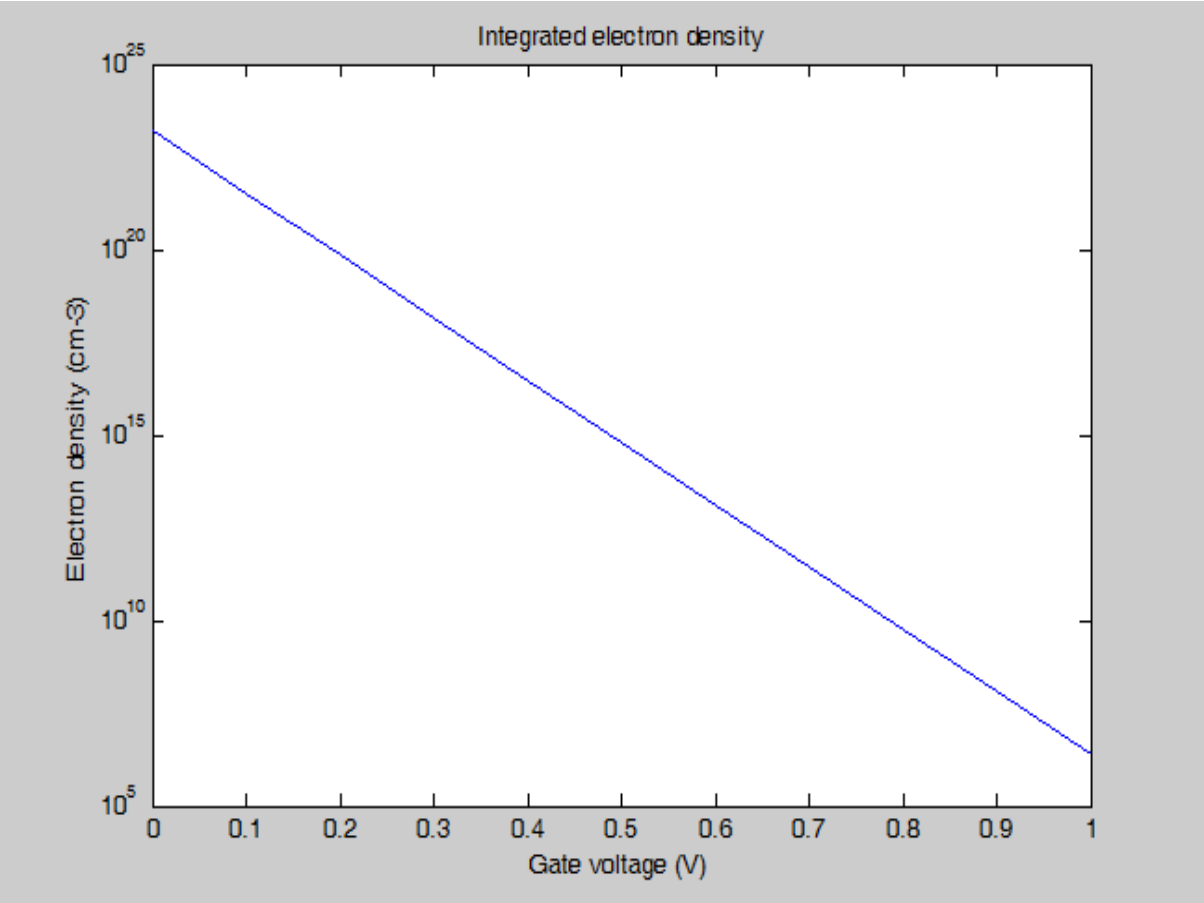
i) When gate voltage = 0 V



i) When gate voltage = 0~0.5V



2. Integrated electron density as a function of gate voltage



‘Integrated electron density is linearly dependent on gate voltage’